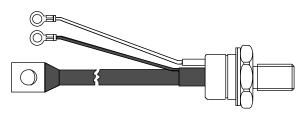
Vishay Semiconductors

Phase Control Thyristors (Stud Version), 110 A



TO-209AC (TO-94)

PRODUCT SUMMARY	
I _{T(AV)}	110 A

FEATURES

- Center gate
- International standard case TO-209AC (TO-94)
- Compression bonded encapsulation for heavy duty operations such as severe thermal cycling
- Hermetic glass-metal case with ceramic insulator (Glass-metal seal over 1200 V)
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS	AND CHARACTERISTICS		
PARAMETER	TEST CONDITIONS	VALUES	UNITS
1		110	А
I _{T(AV)}	T _C	90	°C
I _{T(RMS)}		175	
1	50 Hz	2700	А
I _{TSM}	60 Hz	2830	
l ² t	50 Hz	36.4	kA ² s
1-1	60 Hz	33.2	KA-S
V _{DRM} /V _{RRM}		400 to 1600	V
tq	Typical	100	μs
TJ		- 40 to 125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RA	TINGS			
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE V	I _{DRM} /I _{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA
	04	400	500	
ST110S	08	800	900	20
311103	12	1200	1300	20
	16	1600	1700	



RoHS

COMPLIANT



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ABSOLUTE MAXIMUM RATING		1				
PARAMETER	SYMBOL		TEST CON	DITIONS	VALUES	UNITS
Maximum average on-state current at case temperature	I _{T(AV)}	180° condu	ction, half sine v	wave	110 90	A °C
Maximum RMS on-state current				90 175	C	
Maximum Rivis on-state current	I _{T(RMS)}	DC at 85 °C case temperature				
		t = 10 ms	No voltage		2700	
Maximum peak, one-cycle	I _{TSM}	t = 8.3 ms	reapplied		2830	A kA ² s
non-repetitive surge current	ISM	t = 10 ms	100 % V _{RRM}	Sinusoidal half wave, initial T _J = T _J maximum	2270	
		t = 8.3 ms	reapplied		2380	
	l ² t	t = 10 ms	No voltage reapplied		36.4	
		t = 8.3 ms			33.2	
Maximum I ² t for fusing		t = 10 ms	100 % V _{RRM}		25.8	
		t = 8.3 ms	reapplied		23.5	
Maximum I²√t for fusing	l²√t	t = 0.1 to 10) ms, no voltage	e reapplied	364	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.90	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$), $T_J = T_J maxin$	num	0.92	v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π	$x I_{T(AV)} < I < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	1.79	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)})$), $T_J = T_J$ maxin	num	1.81	mΩ
Maximum on-state voltage	V _{TM}	$I_{pk} = 350 \text{ A}, T_J = T_J \text{ maximum, } t_p = 10 \text{ ms sine pulse}$			1.52	V
Maximum holding current	Ι _Η	T 05 00			600	
Typical latching current	١L	$I_{\rm J} = 25 ^{\circ}{\rm C},$	anode supply 1	2 V resistive load	1000	mA

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega,$ $t_r \leq$ 1 μs T_J = T_J maximum, anode voltage \leq 80 % V_{DRM}	500	A/µs
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C	2.0	
Typical turn-off time	tq	I_{TM} = 100 A, T_J = T_J maximum, dl/dt = 10 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	100	μs

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	20	mA



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TRIGGERING							
PARAMETER	SYMBOL	те	TEAT CONDITIONS				
PARAMETER	STIVIDUL	SYMBOL TEST CONDITIONS					
Maximum peak gate power	P _{GM}	$T_J = T_J$ maximum,	t _p ≤ 5 ms		w		
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50		1	VV	
Maximum peak positive gate current	I _{GM}			2	.0	Α	
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J$ maximum,	$T_J = T_J$ maximum, $t_p \le 5$ ms			v	
Maximum peak negative gate voltage	- V _{GM}		5.0		v		
	I _{GT}	T _J = - 40 °C		180	-		
DC gate current required to trigger		T _J = 25 °C	Maximum required gate trigger/	90	150	mA	
		T _J = 125 °C	current/voltage are the lowest	40	-		
		T _J = - 40 °C	value which will trigger all units	2.9	-		
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C	6 V anode to cathode applied	1.8	3.0	V	
		T _J = 125 °C		1.2	-	1	
DC gate current not to trigger	I _{GD}	TT	Maximum gate current/voltage not to trigger is the maximum	10		mA	
DC gate voltage not to trigger	V _{GD}	$T_J = T_J maximum$	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.25		v	

THERMAL AND MECHANICA	L SPECIFI	CATIONS		
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating junction temperature range	TJ	TJ		°C
Maximum storage temperature range	T _{Stg}		- 40 to 150	
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	0.195	K/W
Maximum thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth, flat and greased	0.08	r./ vv
Mauritian tannua - 10.0/		Non-lubricated threads	15.5 (137)	Nm
Mounting torque, ± 10 %		Lubricated threads	14 (120)	(lbf · in)
Approximate weight			130	g
Case style		See dimensions - link at the end of datasheet	TO-209A	C (TO-94)

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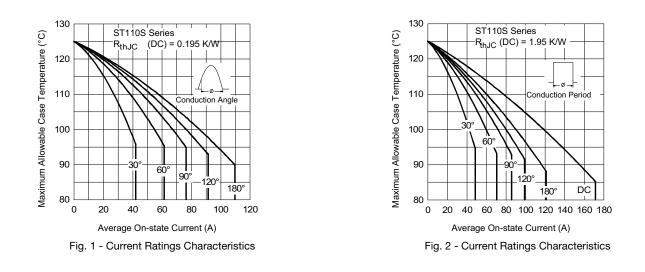
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$\Delta \mathbf{R}_{thJC}$ CONDUCTION	N			
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.035	0.025		
120°	0.041	0.042		
90°	0.052	0.056	$T_J = T_J maximum$	K/W
60°	0.076	0.079		
30°	0.126	0.127		

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



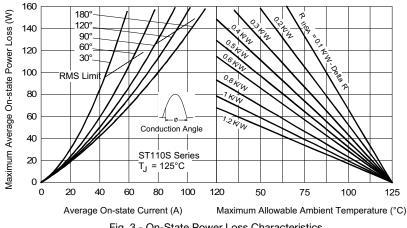
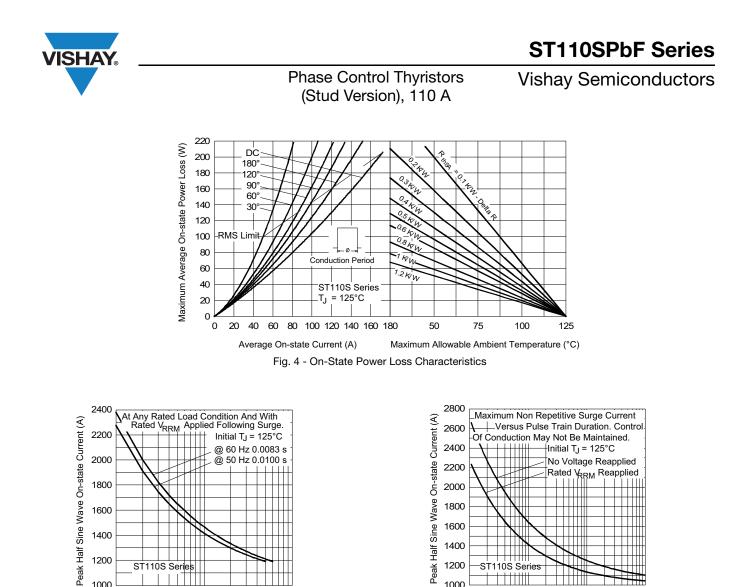


Fig. 3 - On-State Power Loss Characteristics



1400

1200

1000

0.01

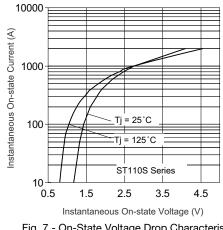
ST110S Series

0.1

Pulse Train Duration (s)

Fig. 6 - Maximum Non-Repetitive Surge Current

1





100

1400

1200

1000

1

ST110S Series

10

Fig. 5 - Maximum Non-Repetitive Surge Current

Number Of Equal Amplitude Half Cycle Current Pulses (N)

10

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Phase Control Thyristors (Stud Version), 110 A



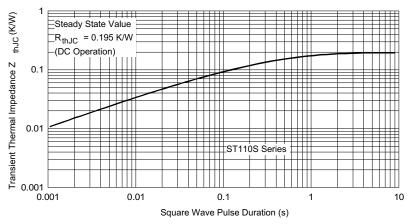
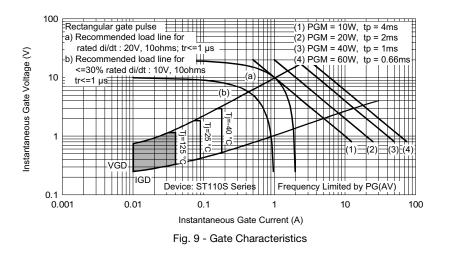


Fig. 8 - Thermal Impedance Z_{thJC} Characteristic





Phase Control Thyristors (Stud Version), 110 A

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ORDERING INFORMATION TABLE

Device code	ST	11	0	S	16	Ρ	0	v	L	PbF
		(2)	(3)	4	(5)	6	(7)	(8)	(9)	(10)
	1	· Thy	vristor	_		-	-	-	-	_
	2	- Ess	ential p	art mark	ing					
	3.	0 =	Conver	ter grad	е					
	4	- S =	Compre	ession b	onding	stud				
	5 -	· Vol	tage coo	le x 100	= V _{RRN}	₄ (see V	oltage I	Ratings	table)	
	6	• P=	Stud ba	ase 20U	NF thre	ads				
	7.	0 =	Eyelet t	erminal	s (gate a	and aux	iliary ca	thode le	eads)	
		1 =	Fast-on	termina	als (gate	and au	ixiliary o	athode	leads)	
		2 =	Flag ter	minals (for cath	ode and	d gate te	erminals	5)	
	8 -	• V	= Glass	s-metal :	seal (on	ly up to	1200 V)		
		• N	lone = C	eramic	housing	(over 1	200 V)			
	9 -	- Crit	ical dV/o	dt:						
		• N	lone = 5	00 V/µs	(standa	ard value	e)			
		• L	= 1000	V/µs (sp	pecial se	election)			
	10 ·	- Lea	nd (Pb)-f	ree						
			L	INKS TO) RELAT	ED DOC	UMENT	S		

Dimensions

www.vishay.com/doc?95078

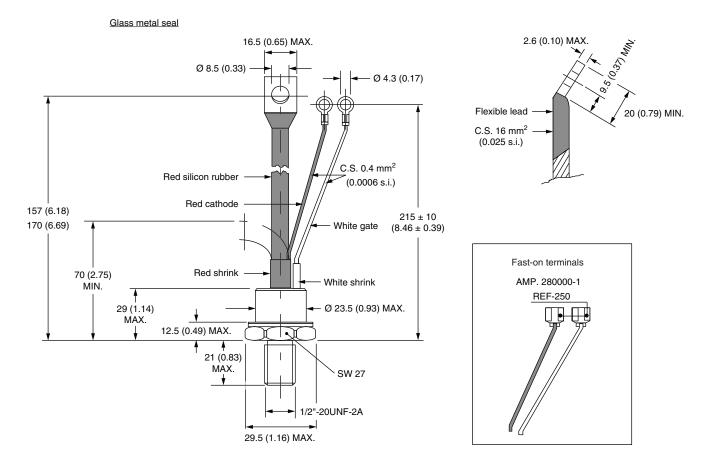
Document Number: 94393 For technical questions within your region, please contact one of the following: Revision: 17-Aug-10 DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com

Vishay Semiconductors

TO-209AC (TO-94) for ST110S Series

DIMENSIONS in millimeters (inches)

SHA



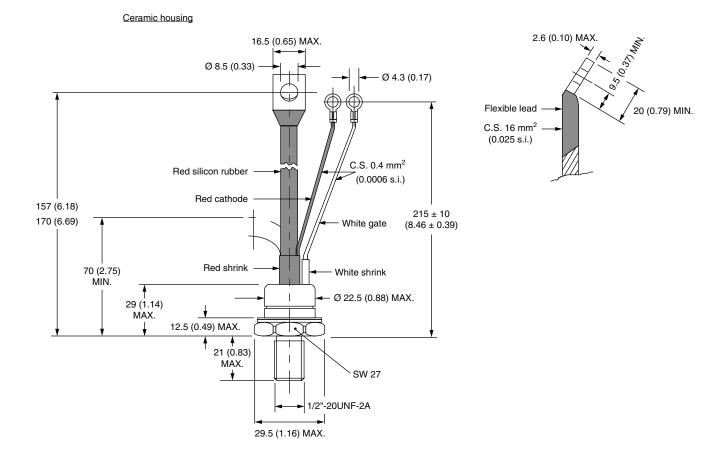
Outline Dimensions

Vishay Semiconductors

TO-209AC (TO-94) for ST110S Series



DIMENSIONS in millimeters (inches)





Vishay

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